Complementary 30 V (D-S) MOSFET

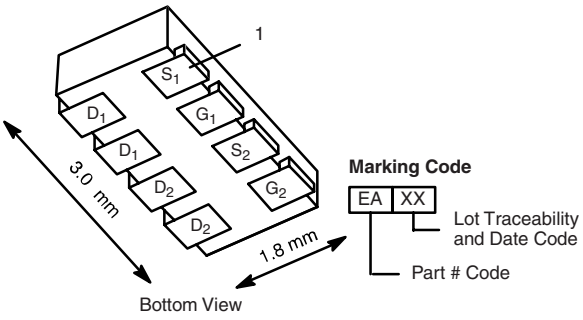
PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
N-Channel	30	0.085 at V_{GS} = 10 V	± 3.9
		0.143 at V_{GS} = 4.5 V	± 3.0
P-Channel	- 30	0.165 at V_{GS} = - 10 V	± 2.8
		0.290 at V_{GS} = - 4.5 V	± 2.1

FEATURES

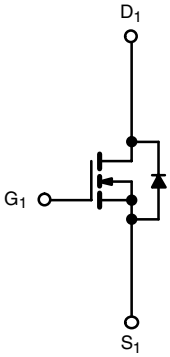
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

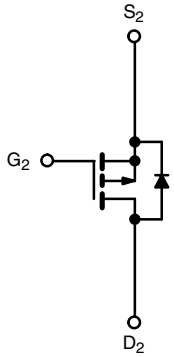
1206-8 ChipFET®



Ordering Information: Si5504DC-T1-E3 (Lead (Pb)-free)
Si5504DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted							
Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V_{DS}	30		- 30		V
Gate-Source Voltage		V_{GS}	± 20				
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	± 3.9	± 2.9	± 2.8	± 2.1	A
	T_A = 85 °C		± 2.8	± 2.1	± 2.0	± 1.5	
Pulsed Drain Current		I_{DM}	± 10				
Continuous Source Current (Diode Conduction)[a]		I_S	1.8	0.9	- 1.8	- 0.9	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2.1	1.1	2.1	1.1	W
	T_A = 85 °C		1.1	0.6	1.1	0.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150				°C
Soldering Recommendations (Peak Temperature)[b, c]			260				

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	50	60	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	30	40	

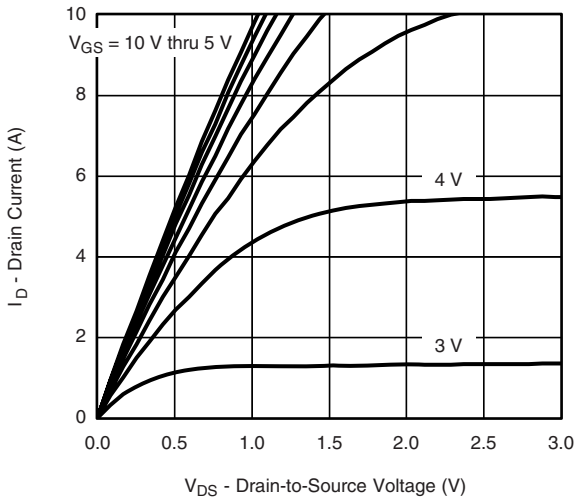
Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. See reliability manual for profile. The ChipFET/PowerPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	1.0			V
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	- 1.0			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	N-Ch			± 100	nA
			P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V	N-Ch			1	µA
		V_{DS} = - 24 V, V_{GS} = 0 V	P-Ch			- 1	
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 85 °C	N-Ch			5	
		V_{DS} = - 24 V, V_{GS} = 0 V, T_J = 85 °C	P-Ch			- 5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	N-Ch	10			A
		V_{DS} ≤ - 5 V, V_{GS} = - 10 V	P-Ch	- 10			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 2.9 A	N-Ch		0.072	0.085	Ω
		V_{GS} = - 10 V, I_D = - 2.1 A	P-Ch		0.137	0.165	
		V_{GS} = 4.5 V, I_D = 2.2 A	N-Ch		0.120	0.143	
		V_{GS} = - 4.5 V, I_D = - 1.6 A	P-Ch		0.240	0.290	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 2.9 A	N-Ch		6		S
		V_{DS} = - 15 V, I_D = - 2.1 A	P-Ch		3		
Diode Forward Voltage[a]	V_{SD}	I_S = 0.9 A, V_{GS} = 0 V	N-Ch		0.8	1.2	V
		I_S = - 0.9 A, V_{GS} = 0 V	P-Ch		- 0.8	- 1.2	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 15 V, V_{GS} = 10 V, I_D = 2.9 A P-Channel V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 2.1 A	N-Ch		5	7.5	nC
			P-Ch		5.5	6.6	
Gate-Source Charge	Q_{gs}		N-Ch		0.8		
			P-Ch		1.2		
Gate-Drain Charge	Q_{gd}		N-Ch		1.0		
			P-Ch		0.9		
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 15 V, R_L = 15 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 6 Ω P-Channel V_{DD} = - 15 V, R_L = 15 Ω I_D ≅ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω	N-Ch		7	11	ns
			P-Ch		8	12	
Rise Time	t_r		N-Ch		12	18	
			P-Ch		11	18	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		12	18	
			P-Ch		14	21	
Fall Time	t_f		N-Ch		7	11	
			P-Ch		8	12	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 0.9 A, dI/dt = 100 A/µs	N-Ch		40	80	
		I_F = - 0.9 A, dI/dt = 100 A/µs	P-Ch		40	80	

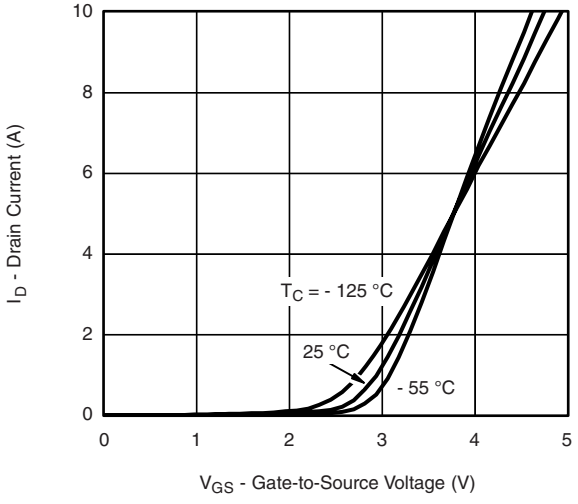
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

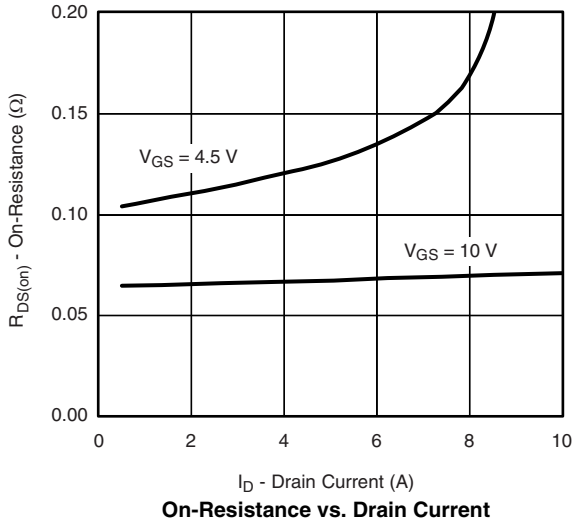
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



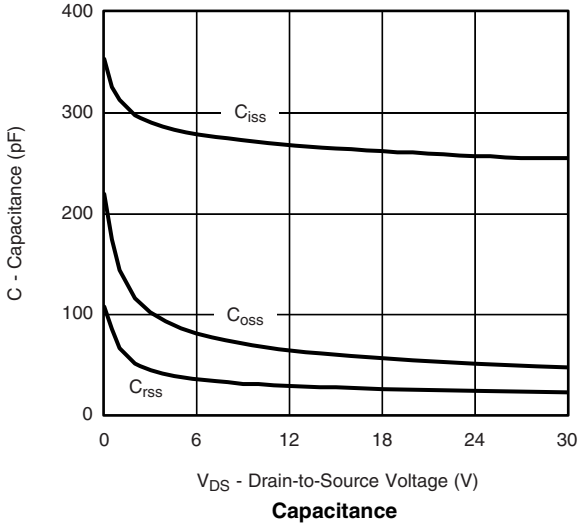
Output Characteristics



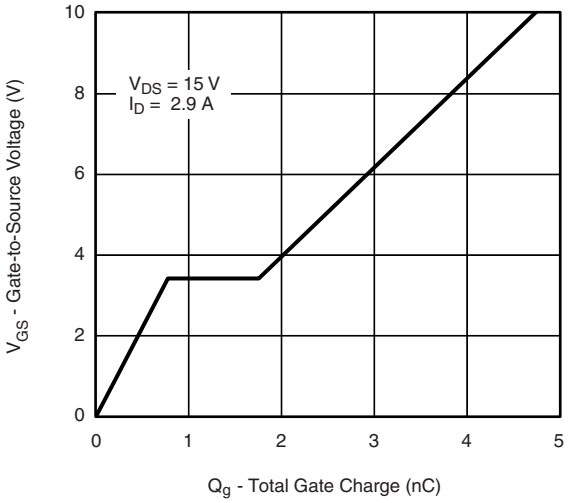
Transfer Characteristics



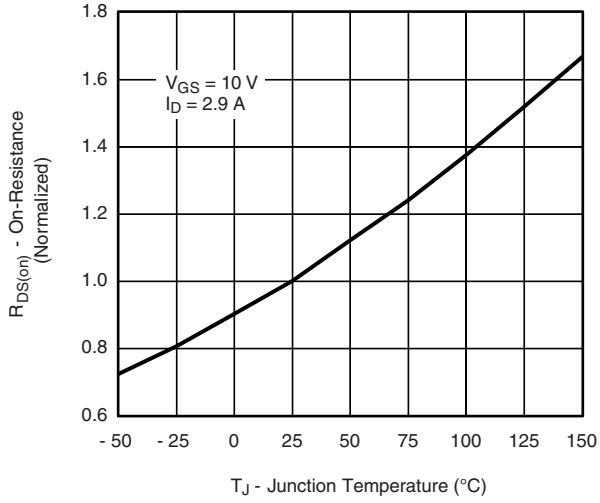
On-Resistance vs. Drain Current



Capacitance

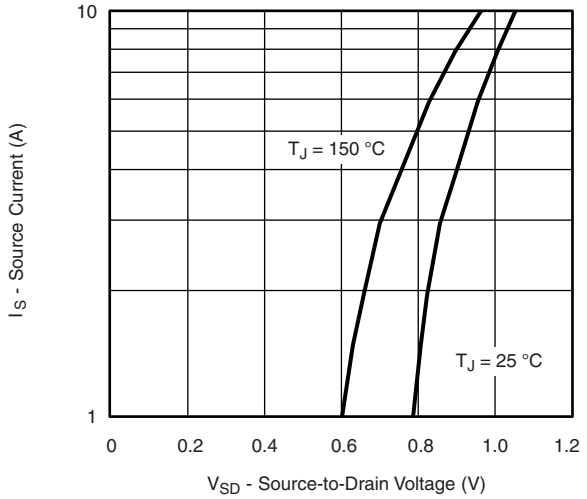


Gate Charge

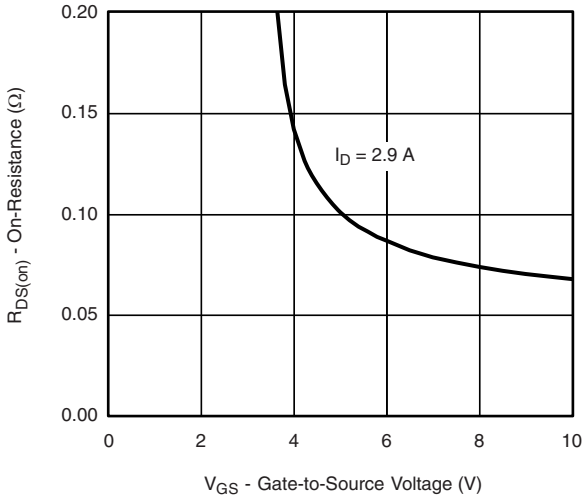


On-Resistance vs. Junction Temperature

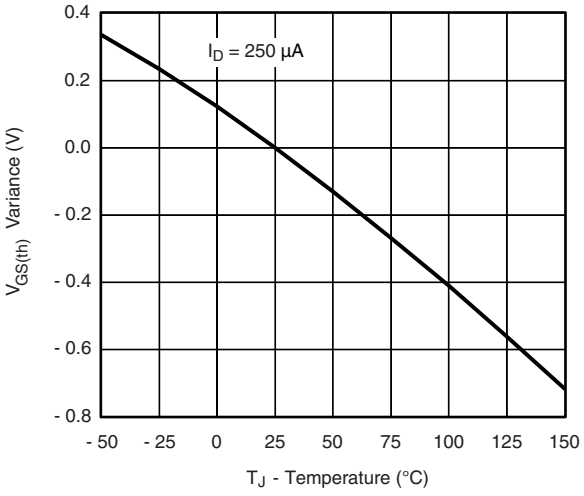
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



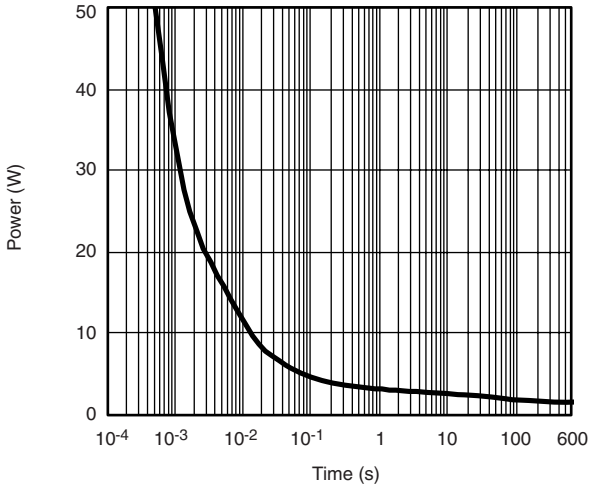
Source-Drain Diode Forward Voltage



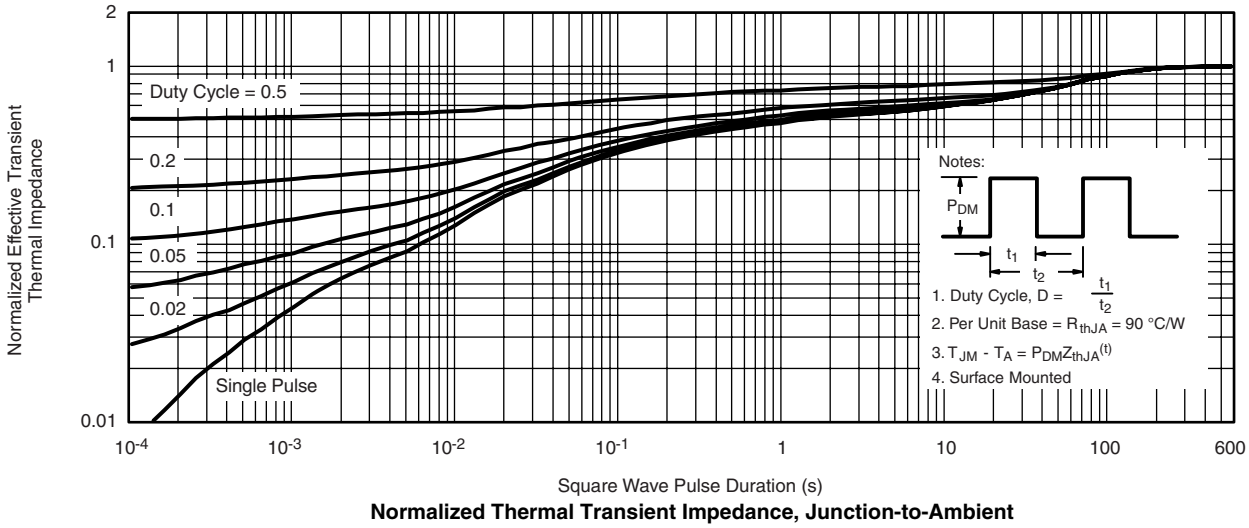
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

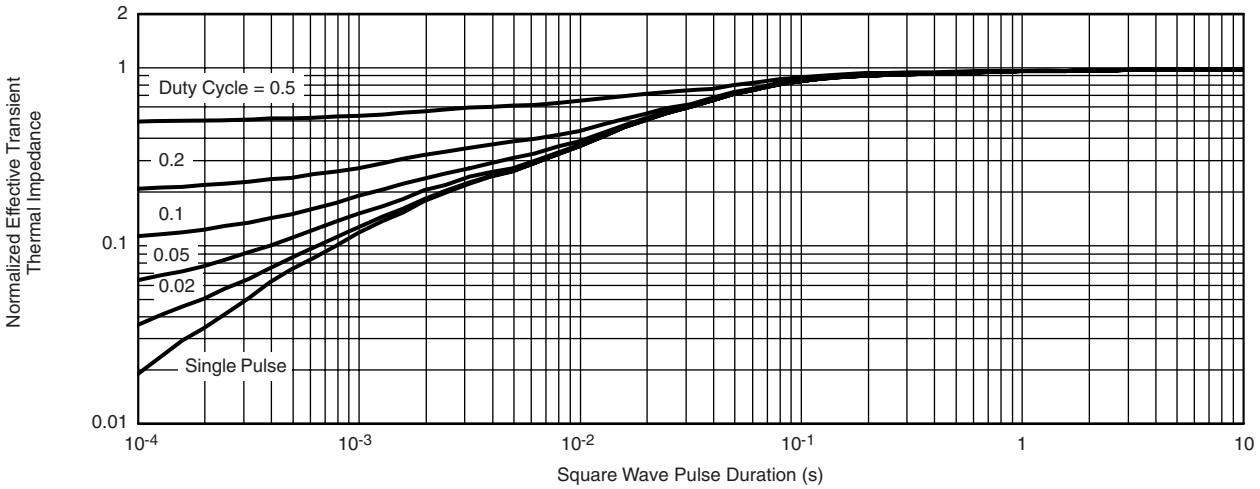


Single Pulse Power



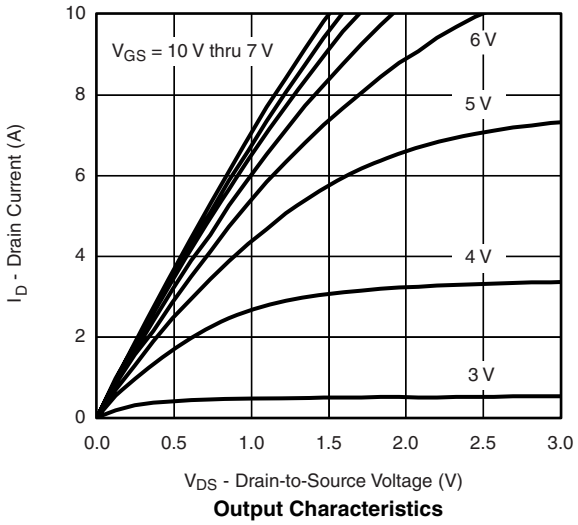
Normalized Thermal Transient Impedance, Junction-to-Ambient

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

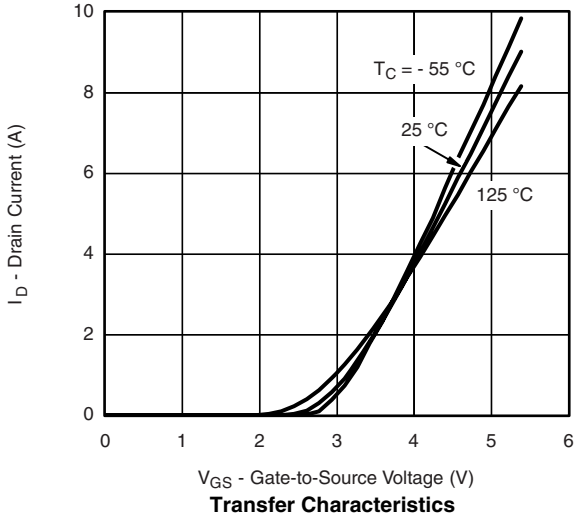


Normalized Thermal Transient Impedance, Junction-to-Foot

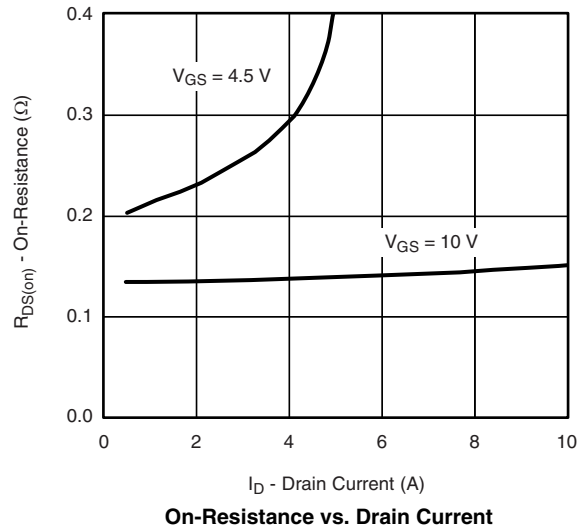
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



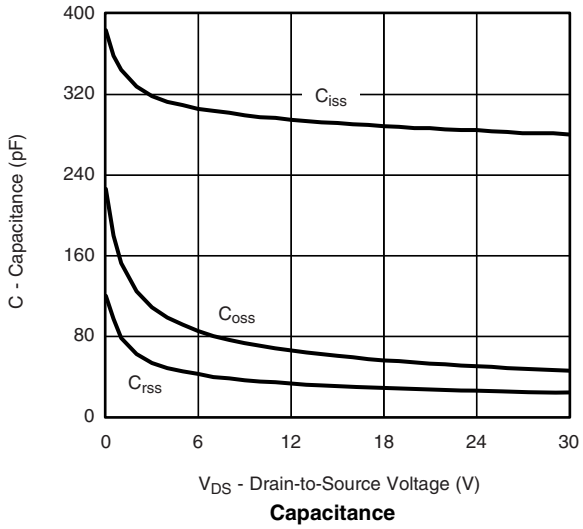
Output Characteristics



Transfer Characteristics

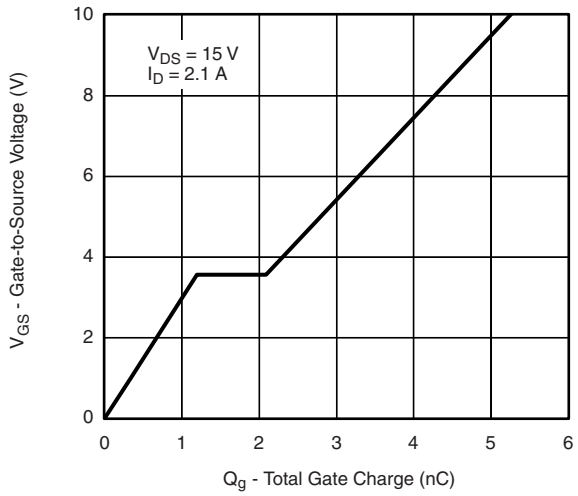


On-Resistance vs. Drain Current

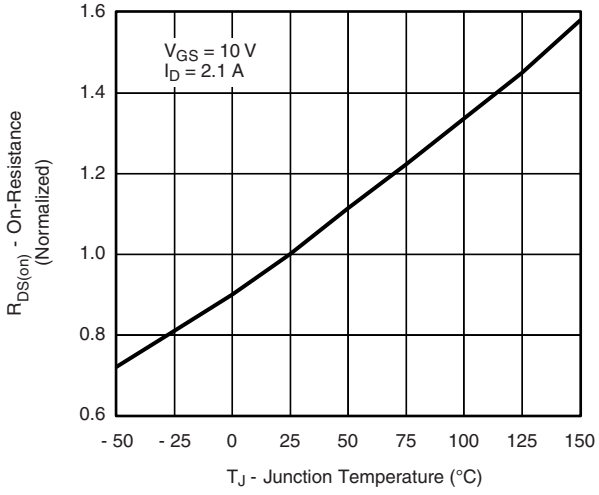


Capacitance

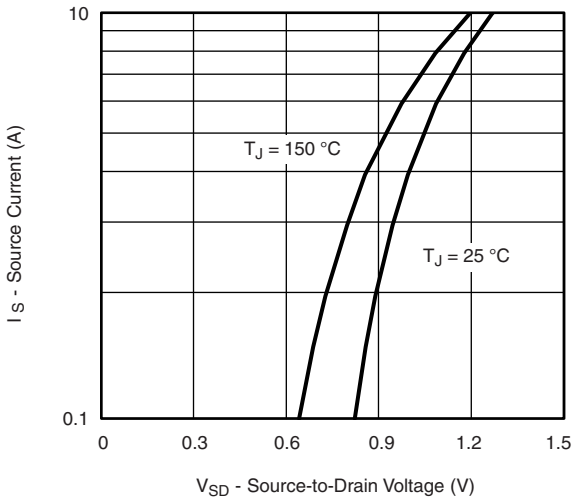
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



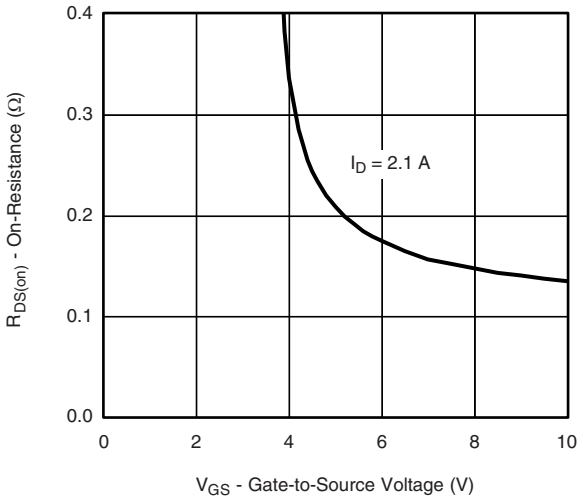
Gate Charge



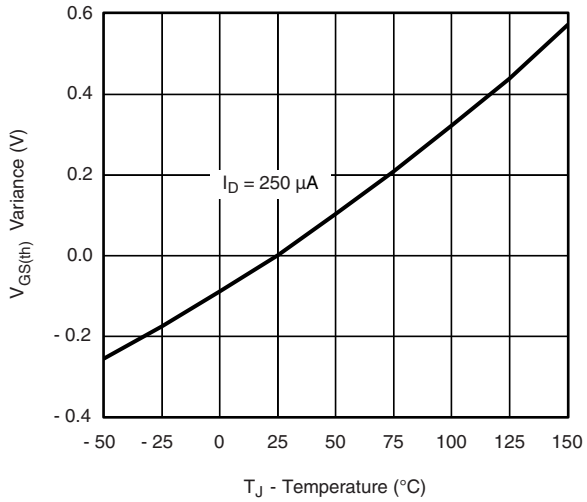
On-Resistance vs. Junction Temperature



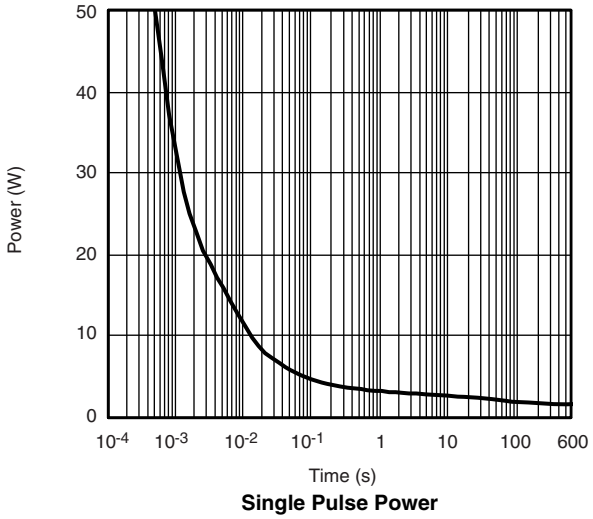
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

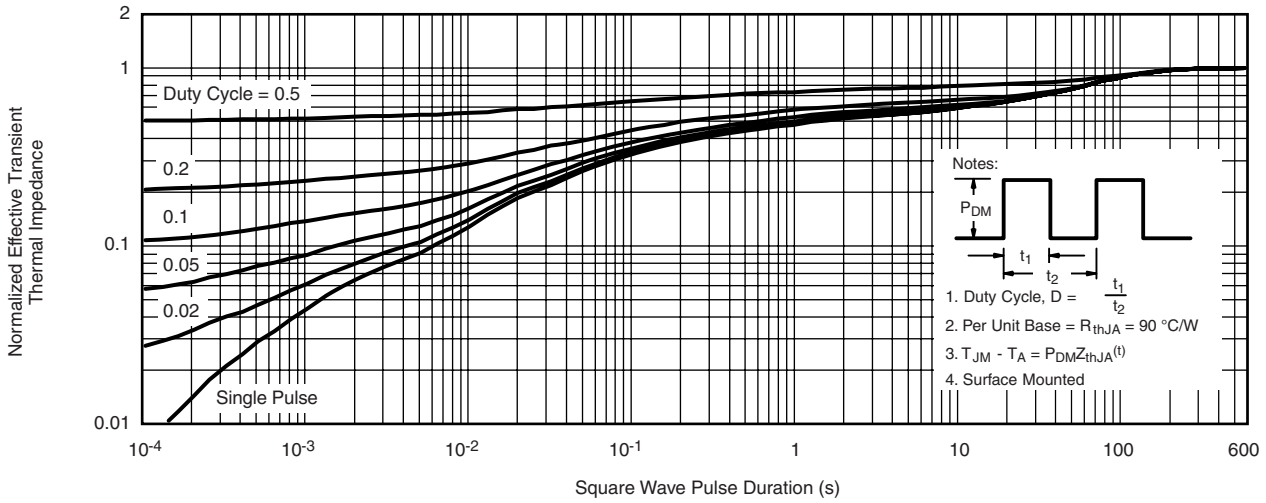


Threshold Voltage

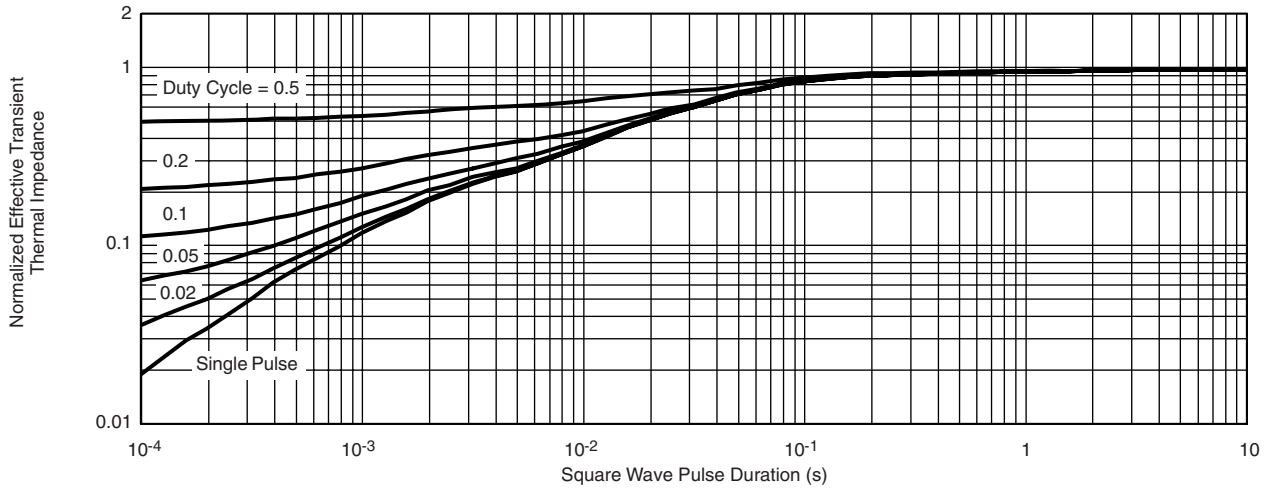


Single Pulse Power

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71056.

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.